

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

1. (Currently Amended) A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 < x < 1$ ), an active layer, a p-type clad layer, and a p-type contact layer, comprising:
  - a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer,
    - wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer, the dopant concentration of the crack-preventing layer being within a range of  $5 \times 10^{16} \text{ cm}^{-3}$  to  $5 \times 10^{17} \text{ cm}^{-3}$ .
- 2.-3. (Canceled)
4. (Original) The light-emitting element according to claim 1, wherein the n-type contact layer has a dopant concentration within a range of  $4 \times 10^{18} \text{ cm}^{-3}$  to  $2 \times 10^{19} \text{ cm}^{-3}$ .
5. (Original) The light-emitting element according to claim 1, wherein a dopant of the crack-preventing layer is either one of Si and Ge.
6. (Original) The light-emitting element according to claim 1, wherein a dopant of the n-type contact layer is either one of Si and Ge.
- 7.-8. (Canceled)

9. (New) The light-emitting element according to claim 1, wherein the light-emitting element comprises a vertical, two-terminal discrete device.

10. (New) The light-emitting element according to claim 1, wherein a driving current light emission of said light emitting element flows in a single direction from a first terminal to a second terminal.